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Hyperfast Rectifier, 4 A FRED Pt®



SlimDPAK (TO-252AE)

LINKS TO ADDITIONAL RESOURCES



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PRIMARY CHARACTERISTICS				
I _{F(AV)}	4 A			
V _R	200 V			
V _F at I _F	0.71 V			
t _{rr} (typ.)	16 ns			
T _J max.	175 °C			
Package	SlimDPAK (TO-252AE)			
Circuit configuration	Single			

FEATURES

- Hyperfast recovery time
- 175 °C max. operating junction temperature
- Low forward voltage drop reduced Q_{rr} and soft recovery
- · Low leakage current
- Very low profile typical height of 1.3 mm
- Ideal for automated placement
- · Polyimide passivation for high reliability standard
- \bullet Meets MSL level 1, per J-STD-020, LF maximum peak of 260 $^{\circ}\mathrm{C}$
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyper fast recovery rectifiers with optimized performance of forward voltage drop and hyper fast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters, or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: SlimDPAK (TO-252AE)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V _{RRM}		200	V
Average rectified forward current	I _{F(AV)}	T _C = 167 °C	4	^
Non-repetitive peak surge current	I _{FSM}	$T_J = 25 \ ^{\circ}C$, 10 ms sine pulse wave	100	A
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	200	-	-		
Forward voltage	V _F	$I_F = 4 A$	-	0.88	1.0	V	
		I _F = 4 A, T _J = 150 °C	-	0.71	0.80		
Reverse leakage current	I _R	$V_{\rm R} = V_{\rm R}$ rated	-	-	3		
		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	80	μA	
Junction capacitance	CT	V _R = 200 V	-	17	-	pF	

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COMPLIANT HALOGEN



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		I_F = 1.0 A, dI_F/dt = 100 A/µs, V_R = 30 V		-	16	-	
Reverse recovery time	+	I _F = 0.5 A, I _R = 1 A, I _{RR} = 0.25 A		-	-	25	
neverse recovery time	t _{rr}	T _J = 25 °C	I _F = 4 A dI _F /dt = 200 A/μs V _R = 160 V	-	20	-	- ns - A
		T _J = 125 °C		-	30	-	
Peak recovery current I _{RRM}		T _J = 25 °C		-	2.5	-	
	IRRM	T _J = 125 °C		-	4	-	
	verse recovery charge Q _{rr}	T _J = 25 °C		-	25	-	nC
neverse recovery charge		T _J = 125 °C		-	60	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to ambient	R _{thJA} ⁽¹⁾⁽²⁾		-	73	90	°C/W
Thermal resistance, junction to mount	R _{thJM} ⁽³⁾		-	2.1	2.5	°C/W
Weight			-	0.20	-	g
Marking device		Case style SlimDPAK (TO-252AE)		4EV	'H02	

Notes

 $^{(1)}$ The heat generated must be less than thermal conductivity from junction to ambient; $dP_D/dT_J < 1R_{thJA}$

⁽²⁾ Free air, mounted or recommended copper pad area; thermal resistance R_{thJA} - junction to ambient

⁽³⁾ Mounted on infinite heatsink

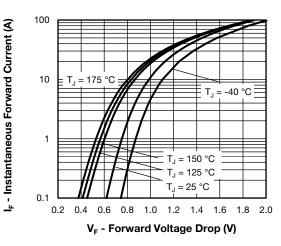


Fig. 1 - Typical Forward Voltage Drop Characteristics

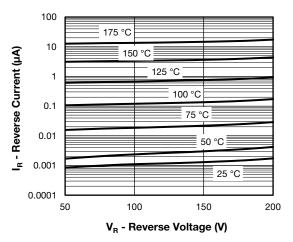


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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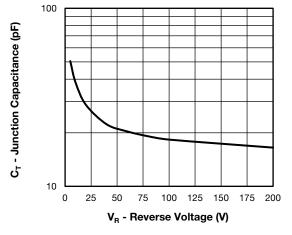


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

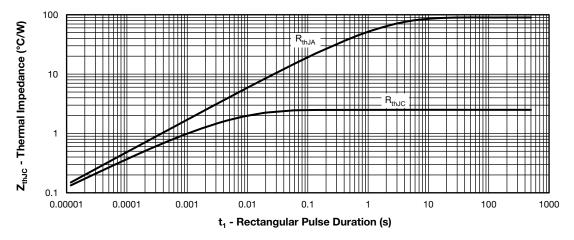


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

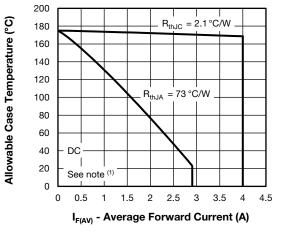
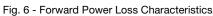


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{I} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

5 4.5 RMS limit Average Power Loss (W) 4 3.5 3 2.5 D = 0.02 D = 0.05 2 D = 0.1 D = 0.2 1.5 D = 0.5 1 DC 0.5 0 3 4 0 2 5 6 I_{F(AV)} - Average Forward Current (A)



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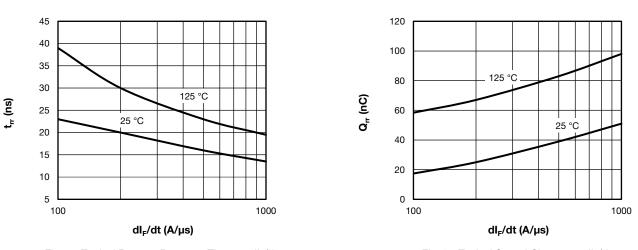


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

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Fig. 8 - Typical Stored Charge vs. dl_F/dt

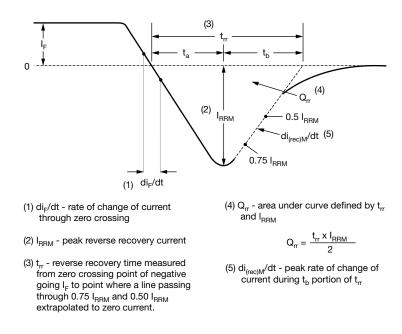


Fig. 9 - Reverse Recovery Waveform and Definitions

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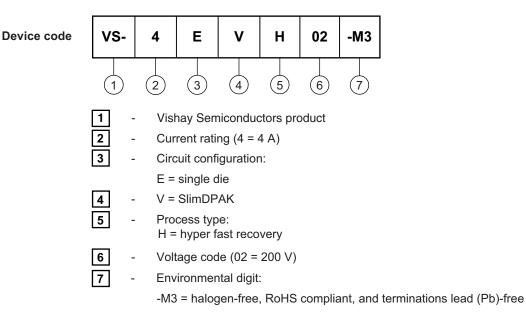
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ORDERING INFORMATION TABLE

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ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-4EVH02-M3/I	4500	4500	13"diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96081			
Part marking information	www.vishay.com/doc?96085			
Packaging information	www.vishay.com/doc?88869			

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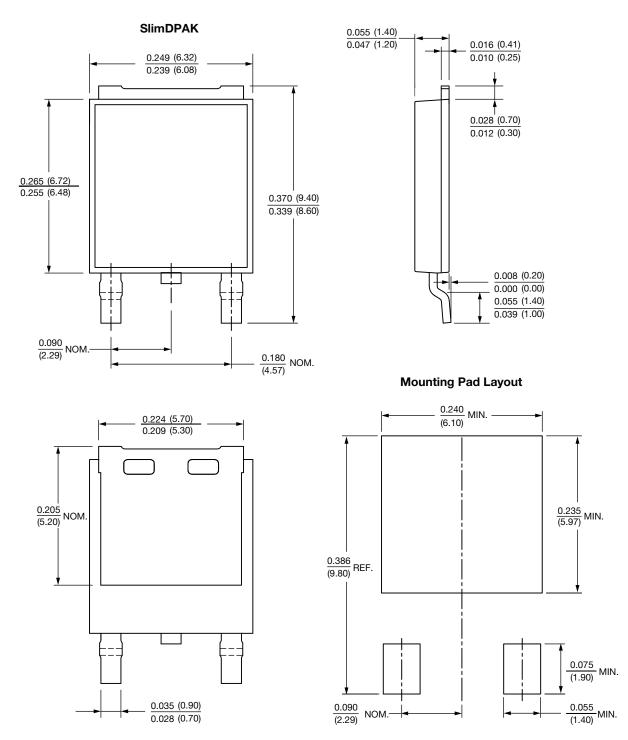


Outline Dimensions

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SlimDPAK

DIMENSIONS in inches (millimeters)



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